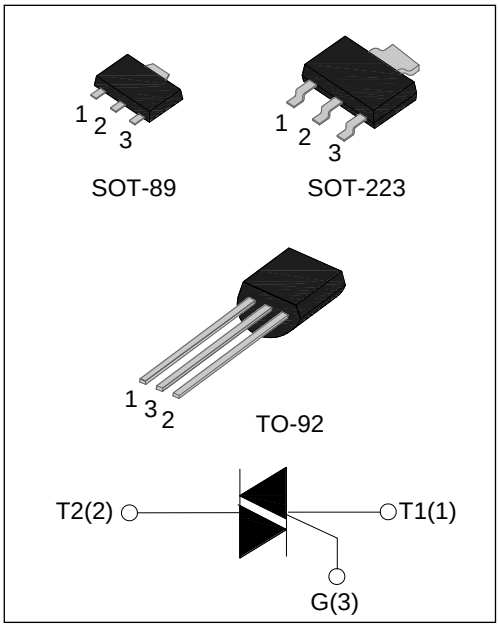
JST131 Series 1A TRIACs

Rev.3.0

DESCRIPTION:

JST131 series triacs with low holding and latching current are especially recommended for use on middle and small resistance type power load.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
I_{TSM}	16	A
V_{TM}	1.7	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	℃
Operating junction temperature range		T_j	-40 - 125	℃
Repetitive peak off-state voltage (T_j=25℃)		V_{DRM}	600/800	V
Repetitive peak reverse voltage (T_j=25℃)		V_{RRM}	600/800	V
Non repetitive surge peak Off-state voltage		V_{DSM}	V_{DRM} + 100	V
Non repetitive peak reverse voltage		V_{RSM}	V_{RRM} + 100	V
RMS on-state current	TO-92 (T_C=51℃)	$I_{T(RMS)}$	1	A
	SOT-89/ SOT-223 (T_C=70℃)			
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	16	A
I^2t value for fusing (tp=10ms)		I^2t	1.28	A^2s
Critical rate of rise of on-state current (I_G=2×I_{GT})		dI/dt	10	A/μs
Peak gate current		I_{GM}	2	A
Average gate power dissipation		$P_{G(AV)}$	0.5	W

Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value		Unit
				T	D	
I_{GT}	V_D=12V R_L=33Ω	Ⅰ-Ⅱ-Ⅲ	MAX	5	5	mA
		Ⅳ		5	10	
V_{GT}		ALL	MAX	1.5		V
V_{GD}	V_D=V_{DRM} T_j=125℃ R_L=3.3KΩ	ALL	MIN	0.2		V
I_L	I_G=1.2I_{GT}	Ⅰ-Ⅲ	MAX	5	5	mA
		Ⅱ-Ⅳ		8	10	
I_H	I_T=200mA		MAX	5	7	mA
dV/dt	V_D=2/3V_{DRM} Gate Open T_j=125℃		MIN	15	20	V/μs

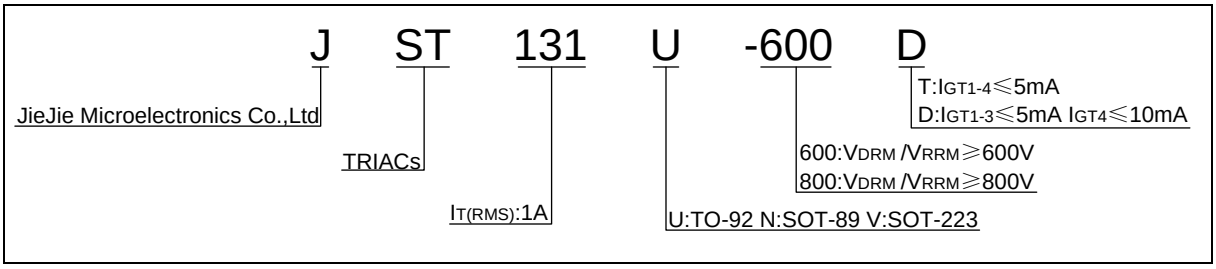
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	I_{TM}=1.4A tp=380μs	T_j=25℃	1.7	V
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25℃	10	μA
I_{RRM}		T_j=125℃	500	μA

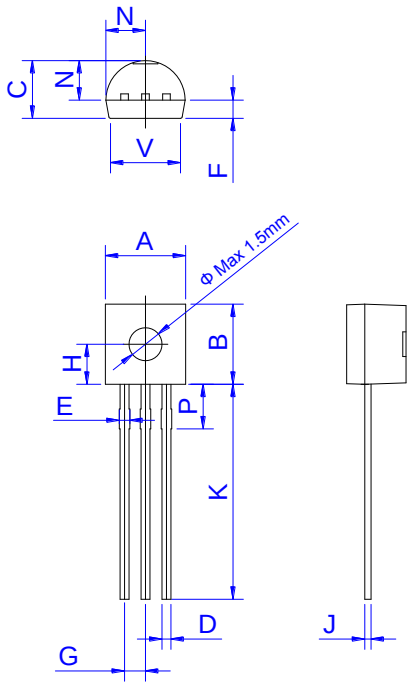
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-92	60	℃/W
		SOT-89/ SOT-223	23	

ORDERING INFORMATION



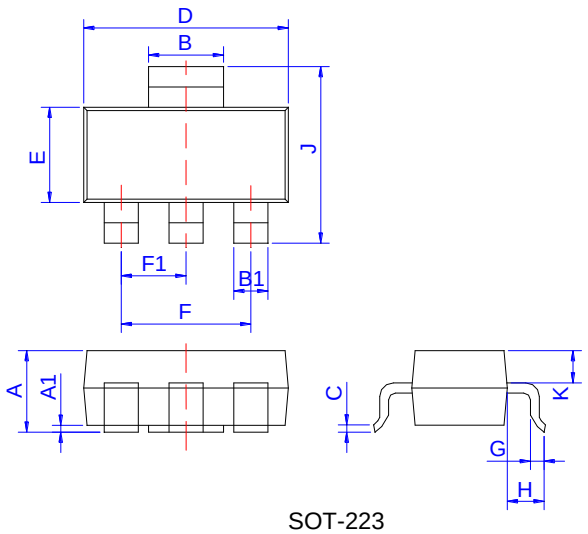
PACKAGE MECHANICAL DATA



TO-92

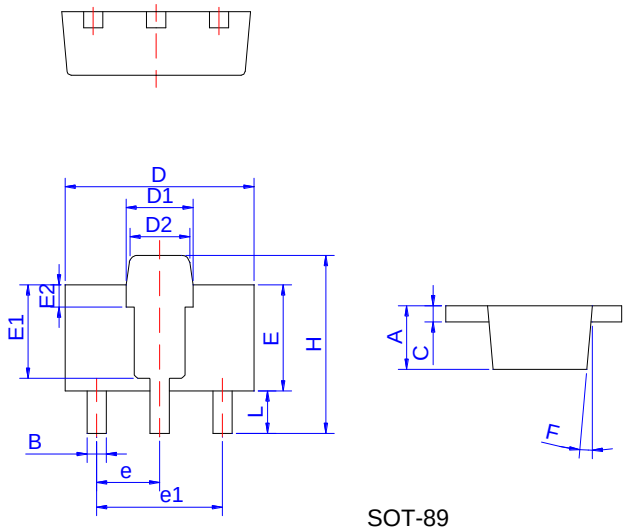
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.60		0.80	0.024		0.031
F	-	1.1	-	-	0.043	-
G	-	1.27	-	-	0.050	-
H	-	2.30	-	-	0.091	-
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.86		2.06	0.073		0.081
V	-		4.3	-		0.169

PACKAGE MECHANICAL DATA



SOT-223

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.5	1.6	1.8	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
E	3.3	3.5	3.7	0.130	0.138	0.146
F		4.6			0.181	
F1		2.3			0.091	
G	0.7	0.9	1.1	0.028	0.035	0.043
H	1.5	1.75	2	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K		0.9			0.035	



SOT-89

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.40		1.60	0.055		0.063
B	0.40		0.52	0.016		0.020
C	0.35		0.41	0.014		0.016
D	4.40		4.60	0.173		0.181
D1	1.50		1.70	0.059		0.067
D2	1.30		1.50	0.051		0.059
E	2.40		2.60	0.094		0.102
E1		2.20			0.087	
E2		0.52			0.020	
e		1.50			0.059	
e1		3.00			0.118	
F		5°			0.197°	
H	4.05		4.25	0.159		0.167
L	0.89		1.20	0.035		0.047

FIG.1 Maximum power dissipation versus RMS on-state current

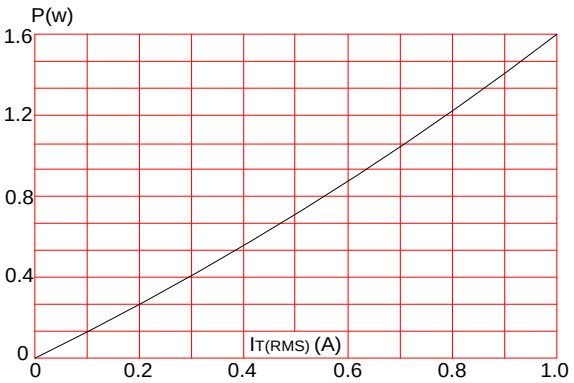


FIG.2: RMS on-state current versus case temperature

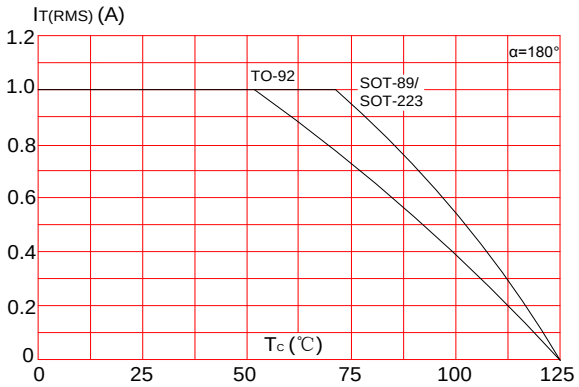


FIG.3: Surge peak on-state current versus number of cycles

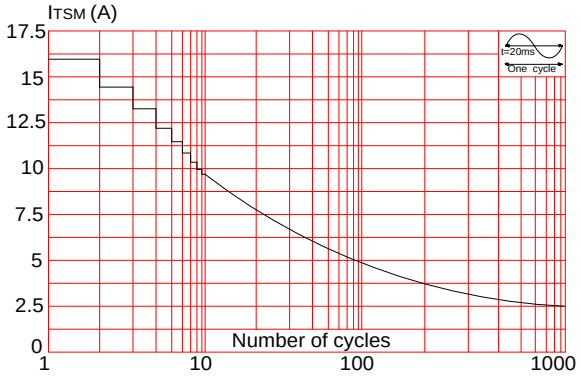


FIG.4: On-state characteristics (maximum values)

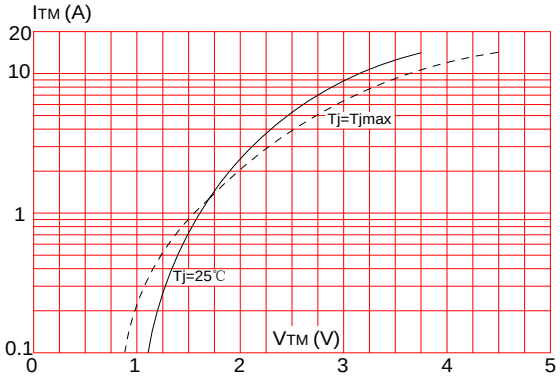


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms and corresponding value of I^2t (dI/dt < 10A/μs)

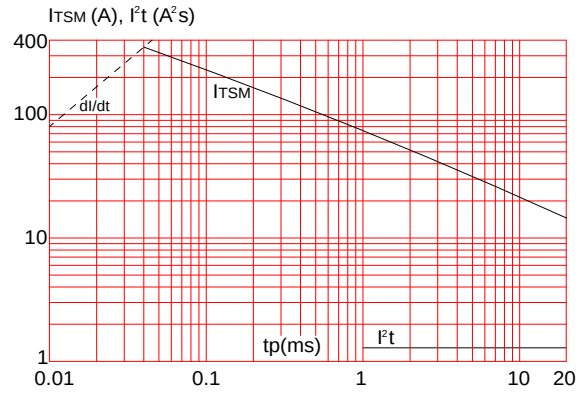
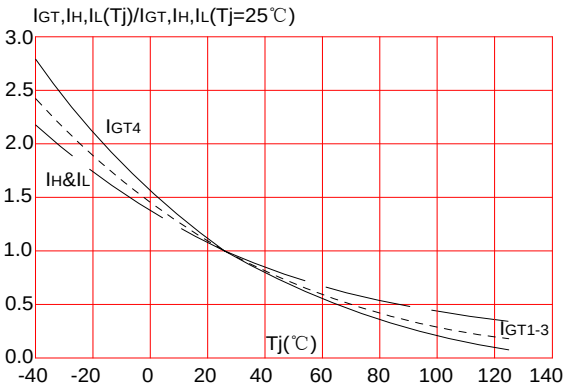


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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